TOSHIBA

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74LCX16245AFT

### LOW-VOLTAGE 16-BIT BUS TRANSCEIVER WITH 5V TOLERANT INPUTS AND OUTPUTS

The TC74LCX16245AFT is a high performance CMOS 16bit BUS TRANSCEIVER. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3V) V<sub>CC</sub> applications, but it could be used to interface to 5V supply environment for both inputs and outputs. This 16bit bus transceiver is controlled by direction control (DIR) inputs and output enable ( $\overline{OE}$ ) inputs which are common to each byte. It can be used as two 8bit transceiver or one 16bit transceiver. The direction of data transmission is determined by the level of the DIR inputs. The  $\overline{OE}$  inputs can be used to disable the device so that the busses are effectively isolated.



Weight : 0.25g (Typ.)

**PIN CONNECTION** 

All inputs are equipped with protection circuits against static discharge.

#### FEATURES

- Low Voltage Operation : V<sub>CC</sub> = 2.0~3.6V
- High Speed Operation :  $t_{pd} = 5.2 \text{ ns} (\text{max.}) \text{ at } V_{CC} = 3.0 \sim 3.6 \text{V}$
- Output Current :  $|I_{OH}| / I_{OL} = 24$ mA (MIN) at  $V_{CC} = 3.0V$
- Latch-up Performance : ± 500mA
- Package : TSSOP

(Thin Shrink Small Outline Package)

- Bidirectional interface between 5V and 3.3V signals.
- Power Down Protection is provided on all inputs and outputs NOTE
- 1) Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.
- .2) All floating (high impedance) bus terminal must have their input level fixed by means of pull up or pull down resistors.

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	<b></b>		
1DIR	10	48	1OE
1B1	2	47	1A1
1B2	3	46	1A2
GND	4	45	GND
1B3	5	44	1A3
1B4	6	43	1A4
Vcc	7	42	Vcc
1B5	8	41	1A5
IB6	9	40	1A6
GND	10	39	GND
1B7	11	38	1A7
1B8	12	37	1A8
2B1	13	36	2A1
2B2	14	35	2A2
GND	15	34	GND
2B3	16	33	2A3
2B4	17	32	2A4
Vcc	18	31	Vcc
2B5	19	30	2A5
2B6	20	29	2A6
GND	21	28	GND
2B7	22	27	2A7
2B8	23	26	2A8
2DIR	24	25	20E

(TOP VIEW)

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#### TRUTH TABLE

INP	INPUT		FUNCTION		
1 <del>0</del> E	1DIR	BUS 1A1-1A8	BUS 1B1-1B8	OUTPUT	
L	L	OUTPUT	INPUT	A = B	
L	Н	INPUT	OUTPUT	B = A	
Н	Х	High Im	Z		

INPUT		FUNC		
2 <del>0</del> E	2DIR	BUS 2A1-2A8	BUS 2B1-2B8	OUTPUT
L	L	OUTPUT	INPUT	A = B
L	н	INPUT	OUTPUT	B = A
Н	Х	High Impedance		Z

X : Don't Care

Z : High impedance

#### IEC LOGIC SYMBOL



#### SYSTEM DIAGRAM



961001EBA2'

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#### MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT	
Power Supply Voltage	V <sub>CC</sub>	-0.5~7.0	V	
DC Input Voltage (DIR, OE)	VIN	-0.5~7.0	V	
DC Bus I/O Voltage	Vicio	-0.5~7.0 (Note 1)	v	
DC Bus 170 Voltage	VI/O	-0.5~V <sub>CC</sub> +0.5 (Note 2)		
Input Diode Current	IIК	- 50	mA	
Output Diode Current	Іок	±50 (Note 3)	mA	
DC Output Current	Ιουτ	± 50	mA	
Power Dissipation	PD	400	mW	
DC V <sub>CC</sub> /Ground Current Per Supply Pin	ICC/IGND	± 100	mA	
Storage Temperature	T <sub>stg</sub>	- 65~150	°C	

(Note 1) Output in Off-State

(Note 2) High or Low State. IOUT absolute maximum rating must be observed.

(Note 3) V<sub>OUT</sub><GND, V<sub>OUT</sub>>V<sub>CC</sub>

#### **RECOMMENDED OPERATING RANGE**

PARAMETER	SYMBOL	RATING	UNIT		
Supply Voltage	Maa	2.0~3.6	v		
Supply Voltage	VCC	V <sub>CC</sub> 1.5~3.6 (Note 4)			
Input Voltage (DIR, OE)	VIN	0~5.5	V		
Bus I/O Voltage	N/ / a	0~5.5 (Note 5)	v		
Bus 170 Voltage	VI/O	0~ V <sub>CC</sub> (Note 6)	v		
Output Current		±24 (Note 7)			
Output Current	IOH / IOL	± 12 (Note 8)	mA		
Operating Temperature	T <sub>opr</sub>	- 40~85	°C		
Input Rise And Fall Time	dt/dv	0~10 (Note 9)	ns / V		

- (Note 4) Data Retention Only
- (Note 5) Output in Off-State
- (Note 6) High or Low State
- (Note 7)  $V_{CC} = 3.0 \sim 3.6V$
- (Note 8)  $V_{CC} = 2.7 \sim 3.0V$
- (Note 9)  $V_{IN} = 0.8 \sim 2.0 V$ ,  $V_{CC} = 3.0 V$

### ELECTRICAL CHARACTERISTICS

DC characteristics (Ta =  $-40 \sim 85^{\circ}$ C)

PARA	METER	SYMBOL	TEST	CONDITION	V <sub>CC</sub> (V)	MIN.	MAX.	UNIT																								
Input	"H" Level	VIH			2.7~3.6	2.0	_	V																								
Voltage	"L" Level	VIL			2.7~3.6	_	0.8	V																								
				l <sub>OH</sub> = – 100μA	2.7~3.6	V <sub>CC</sub> - 0.2	_																									
Output	"H" Level	∨он	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = – 12mA	2.7	2.2		V																								
Output				I <sub>OH</sub> = – 18mA	3.0	2.4																										
Voltage				I <sub>OH</sub> = - 24mA	3.0	2.2	_																									
			N/	l <sub>OL</sub> = 100μA	2.7~3.6	_	0.2																									
	"L" Level	Max	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 12mA	2.7	_	0.4	v																								
	L Levei	VOL																				AIH OL AIL	VIH OL VIL			VIH OF VIL	ALH OL ALL		I <sub>OL</sub> = 16mA	3.0	_	0.4
				I <sub>OL</sub> = 24mA	3.0	_	0.55																									
Input Leaka	age Current	<sup>I</sup> IN	V <sub>IN</sub> = 0~5.5V		2.7~3.6	_	± 5.0	μA																								
3-State Out Off-State C	-	loz	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = 0~5.5V		2.7~3.6	—	± 5.0	μΑ																								
Power Off Current	Leakage	lOFF	V <sub>IN</sub> / V <sub>OUT</sub> = 5.5V		0	_	10.0	μΑ																								
Quiescent S	Supply	1	VIN = VCC C	or GND	2.7~3.6	_	20.0																									
Current		lcc	$V_{IN} / V_{OUT} = 3.6 \sim 5.5 V$		2.7~3.6	_	±20.0	μΑ																								
Increase In Input	I <sub>CC</sub> Per	∆ا	$V_{\rm IH} = V_{\rm CC} - 0.6V$		2.7~3.6		500	μΑ																								

AC characteristics (Ta =  $-40 \sim 85^{\circ}$ C)

PARAMETER	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	MIN.	MAX.	UNIT
Propagation Delay	t <sub>pLH</sub>	(Fig.1, 2)	2.7	_	6.2	
Time	t <sub>pHL</sub>		3.3±0.3	1.5	5.2	ns
3-State Output Enable	t <sub>pZL</sub>	(Fig.1, 3)	2.7	_	7.5	
Time	t <sub>pZH</sub>		3.3±0.3	1.5	6.5	ns
3-State Output Disable	t <sub>pLZ</sub>	(Fig.1, 3)	2.7	_	7.0	
Time	t <sub>pHZ</sub>		3.3±0.3	1.5	6.0	ns
Output To Output	tosLH	(Note 10)	2.7	_	_	20
Skew	t <sub>osHL</sub>		3.3±0.3	_	1.0	ns

(Note 10) Parameter guaranteed by design.

 $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$ 

Dynamic switching characteristics

(Ta = 25°C, Input  $t_r = t_r = 2.5$ ns, CL = 50pF, RL = 500 $\Omega$ )

PARAMETER	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	ТҮР	UNIT
Quiet Output Maximum Dynamic VOL	V <sub>OLP</sub>	V <sub>IH</sub> = 3.3V, V <sub>IL</sub> = 0V	3.3	0.8	V
Quiet Output Minimum Dynamic VOL	νοιν	V <sub>IH</sub> = 3.3V, V <sub>IL</sub> = 0V	3.3	0.8	V

Capacitive characteristics  $(Ta = 25^{\circ}C)$ 

PARAMETER	SYMBOL	TEST CON	DITION	V <sub>CC</sub> (V)	ТҮР	UNIT
Input Capacitance	C <sub>IN</sub>	DIR, OE		3.3	7	рF
Bus Input Capacitance	C <sub>I/O</sub>	An, Bn		3.3	8	pF
Power Dissipation Capacitance	C <sub>PD</sub>	f <sub>IN</sub> = 10MHz	(Note 11)	3.3	25	pF

(Note 11) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation :

 $I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16.$  (Per bit)

## **TOSHIBA**

Fig.1 Test circuit



PARAMETER	SWITCH
t <sub>pLH</sub> , t <sub>pHL</sub>	Open
t <sub>pLZ</sub> , t <sub>pZL</sub>	6.0V
t <sub>pHZ</sub> , t <sub>pZH</sub>	GND

#### AC WAVEFORM

Fig.2 t<sub>pLH</sub>, t<sub>pHL</sub>



### Fig.3 t<sub>pLZ</sub>, t<sub>pHZ</sub>, t<sub>pZL</sub>, t<sub>pZH</sub>



#### OUTLINE DRAWING TSSOP48-P-0061-0.50





Weight : 0.25g (Typ.)